

6367255 MOTOROLA SC (DIODES/OPTO)

34C 38152 D

T-25-11

SILICON THYRISTOR DIE (continued)

DIE NO. 2C5060
LINE SOURCE — DTL60



SCR-Silicon Controlled Rectifier

Device assembled from this die type are similar to the following device types:

- 2N5060
- 2N5061
- 2N5062
- MCR101
- MCR102
- MCR103
- MCR104

Backside: Anode

METALLIZATION —

Top Al

Back Au

GOLD THICKNESS 3000 Å

DIE THICKNESS 6 ± 2

BONDING PAD SIZE —

Cathode 13x13 mils

Gate 4.0 x 4.0 mils

11

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$; Note 1, $R_{GK} = 1.0\text{ k}\Omega$)

Parameter	Test Conditions	Min	Max	Unit
I_{RRM}, I_{DRM}	$V_D = 30\text{ Vdc}$	—	10	μAdc
V_{TM}	$I_{TM} = 1.0\text{ Adc peak}$	—	1.7	Volts
V_{GT}	continuous dc	—	0.8	Volts
I_H	$V_A = 7.0\text{ Vdc}, I_{AI} = 20\text{ mAdc}$	—	5.0	mAdc
I_{GT}	$V_A = 7.0\text{ Vdc}, R_L = 100\ \Omega$	—	200	μAdc

- NOTES: 1. Because of the limitations of probe testing, only dc parameters are tested. These parameters must be measured using pulse techniques: pulse width $\leq 1.0\text{ ms}$, duty cycle $\leq 1\%$.
2. Detailed device characteristics are available from your Motorola sales representative.